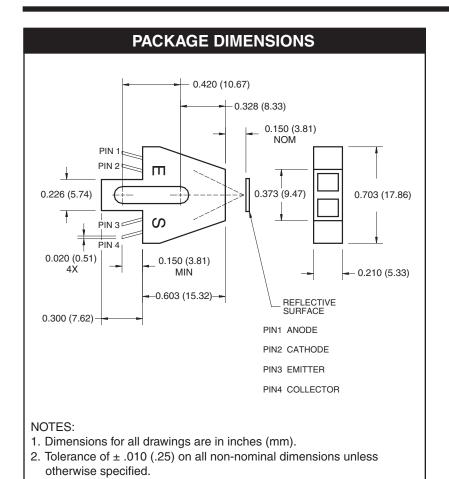
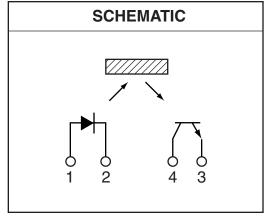


## QRB1113 QRB1114







#### **DESCRIPTION**

The QRB1113/1114 consists of an infrared emitting diode and an NPN silicon phototransistor mounted side by side on a converging optical axis in a black plastic housing. The phototransistor responds to radiation from the emitting diode only when a reflective object passes within its field of view. The area of the optimum response approximates a circle .200" in diameter.

### **FEATURES**

- · No contact surface sensing
- Phototransistor output
- · Focused for sensing specular reflection
- · Daylight filter on photosensor
- Dust cover



# QRB1113 QRB1114

Parameter	Symbol	Rating	Units °C	
Operating Temperature	T <sub>OPR</sub>	-40 to +85		
Storage Temperature	T <sub>STG</sub>	-40 to +85	°C	
Soldering Temperature (Iron) <sup>(2,3,4)</sup>	T <sub>SOL-I</sub>	240 for 5 sec	°C	
Soldering Temperature (Flow) <sup>(2,3)</sup>	T <sub>SOL-F</sub>	260 for 10 sec	°C	
EMITTER				
Continuous Forward Current	I <sub>F</sub>	50	mA	
Reverse Voltage	V <sub>R</sub>	5	V	
Power Dissipation <sup>(1)</sup>	P <sub>D</sub>	100	mW	
SENSOR				
Collector-Emitter Voltage	V <sub>CEO</sub>	30	V	
Emitter-Collector Voltage	V <sub>ECO</sub>	4.5	V	
Collector Current		20	mA	
Power Dissipation <sup>(1)</sup>	P <sub>D</sub>	100	mW	

### **NOTES**

- 1. Derate power dissipation linearly 1.67 mW/°C above 25°C.
- 2. RMA flux is recommended.
- Methanol or isopropyl alcohols are recommended as cleaning agents.
  Soldering iron 1/16" (1.6mm) minimum from housing.

- D is the distance from the assembly face to the reflective surface.
  Measured using an Eastman Kodak neutral test card with 90% diffused reflecting surface.
  Cross talk is the photo current measured with current to the input diode and no reflecting surface.

ELECTRICAL/OPTICAL CHARACTERISTICS (T <sub>A</sub> = 25°C)									
Parameter	Test Conditions	Symbol	Min.	Тур.	Max.	Units			
EMITTER									
Forward Voltage	I <sub>F</sub> = 40 mA	V <sub>F</sub>	_	_	1.7	V			
Reverse Current	V <sub>R</sub> = 5.0 V	I <sub>R</sub>	_	_	100	μΑ			
Peak Emission Wavelength	I <sub>F</sub> = 20 mA	λ <sub>PE</sub>	_	940	_	nm			
SENSOR									
Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 1 mA	BV <sub>CEO</sub>	30	_	_	V			
Emitter-Collector Breakdown Voltage	I <sub>E</sub> = 0.1 mA	BV <sub>ECO</sub>	5	_	_	V			
Collector-Emitter Dark Current	$V_{CE} = 10 \text{ V}, I_{F} = 0 \text{ mA}$	I <sub>CEO</sub>	_	_	100	nA			
COUPLED									
On-state Collector Current	I <sub>F</sub> = 40 mA, V <sub>CE</sub> = 5 V								
QRB1113	$D = .150^{\circ(5,6)}$	I <sub>C(ON)</sub>	0.20	_	_	mA			
QRB1114	D = .150 (***)		0.60	_					
Collector-Emitter	$I_{\rm F} = 20 \text{ mA}, I_{\rm C} = 0.5 \text{ mA}$	V <sub>CE (SAT)</sub>		_	0.4	V			
Saturation Voltage	1 <sub>F</sub> = 20 111, 1 <sub>C</sub> = 0.0 111, 1								
Rise Time	$V_{CE} = 5 \text{ V}, R_{L} = 100 \text{ V}$	t <sub>r</sub>	_	8	_	110			
Fall Time	$I_{C(ON)} = 5 \text{ mA}$	t <sub>f</sub>	_	8	_	μs			
Cross Talk	$I_F = 40 \text{ mA}, V_{CE} = 5 V^{(7)}$	I <sub>CX</sub>	_	_	1.00	μΑ			

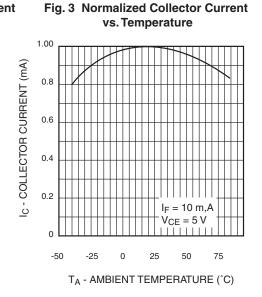
# QRB1113 QRB1114

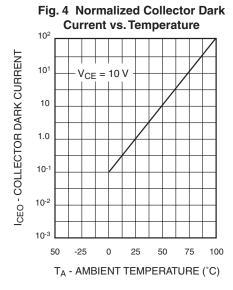
## **TYPICAL PERFORMANCE CURVES**

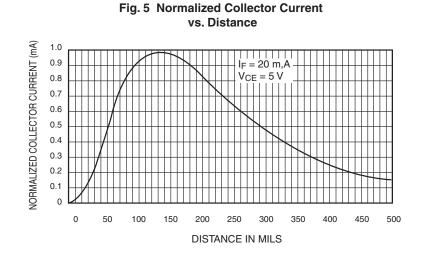
Fig. 1 Forward Voltage vs. Forward Current 1.60 1.40 VF - FORWARD VOLTAGE (V) 1.20 1.00 0.80 0.60 0.40 0.20 0.1 1.0 10 100 IF - FORWARD CURRENT (mA)

Fig. 2 Normalized Collector Current vs. Forward Current 10.0 I<sub>C</sub> - COLLECTOR CURRENT (mA) 1.00 0.10 0.01  $V_{CE} = 5 V$ D = .05" .001 0.0 10 20 30 40 50

IF - FORWARD CURRENT (mA)









## QRB1113 QRB1114

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